## Product Preview

# Quad 2-Input OR Gate / CMOS Logic Level Shifter

with LSTTL-Compatible Inputs

The MC74VHCT32A is an advanced high speed CMOS 2-input OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

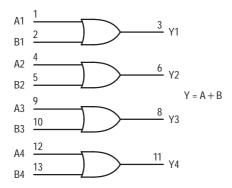
The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The device input is compatible with TTL-type input thresholds and the output has a full 5V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3.0V CMOS logic to 5.0V CMOS Logic or from 1.8V CMOS logic to 3.0V CMOS Logic while operating at the high-voltage power supply.

The MC74VHCT32A input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHCT32A to be used to interface 5V circuits to 3V circuits. The output structures also provide protection when  $V_{CC} = 0V$ . These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

- High Speed: tpD = 3.8ns (Typ) at  $V_{CC} = 5V$
- Low Power Dissipation:  $I_{CC} = 2\mu A$  (Max) at  $T_A = 25$ °C
- TTL-Compatible Inputs:  $V_{II} = 0.8V$ ;  $V_{IH} = 2.0V$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: VOLP = 0.8V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V

#### LOGIC DIAGRAM



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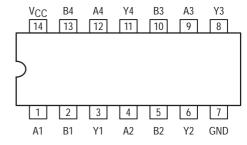


14-LEAD SOIC D SUFFIX CASE 751A 14-LEAD TSSOP DT SUFFIX CASE 948G



14-LEAD SOIC EIAJ M SUFFIX CASE 965

# PIN CONNECTION AND MARKING DIAGRAM (Top View)



For detailed package marking information, see the Marking Diagram section on page 4 of this data sheet.

#### **FUNCTION TABLE**

Inp	uts	Output
A B		Υ
L	L	L
L	Н	Н
Н	L	Н
Н	Н	Н

#### ORDERING INFORMATION

Device	Package	Shipping
MC74VHCT32AD	SOIC	55 Units/Rail
MC74VHCT32ADT	TSSOP	96 Units/Rail
MC74VHCT32AM	SOIC EIAJ	50 Units/Rail

#### **MAXIMUM RATINGS\***

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage	- 0.5 to + 7.0	V
V <sub>out</sub>	DC Output Voltage $V_{CC} = 0$ High or Low State	- 0.5 to + 7.0 - 0.5 to V <sub>CC</sub> + 0.5	V
lik	Input Diode Current	- 20	mA
lok	Output Diode Current (V <sub>OUT</sub> < GND; V <sub>OUT</sub> > V <sub>CC</sub> )	± 20	mA
l <sub>out</sub>	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V <sub>CC</sub> and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, Vin and Vout should be constrained to the range GND  $\leq$  (V<sub>in</sub> or V<sub>out</sub>)  $\leq$  V<sub>CC</sub>.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V<sub>CC</sub>). Unused outputs must be left open.

†Derating — SOIC Packages: – 7 mW/ $^{\circ}$ C from 65 $^{\circ}$  to 125 $^{\circ}$ C TSSOP Package: - 6.1 mW/°C from 65° to 125°C

#### RECOMMENDED OPERATING CONDITIONS

TSSOP Package: – 6.1 mW/°C from 65° to 125°C		其是		
RECOMMENDED OPERATING CONDITIONS	7c 3	-0		
Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	Vcc	2.0	5.5	V
DC Input Voltage	VIN	0.0	5.5	V
DC Output Voltage V <sub>CC</sub> = 0 High or Low State	VOUT	0.0 0.0	5.5 VCC	V
Operating Temperature Range	TA	-55	+85	°C
Input Rise and Fall Time $V_{CC} = 3.3V \pm 0.3V$ $V_{CC} = 5.0V \pm 0.5V$	t <sub>r</sub> , t <sub>f</sub>	0 0	100 20	ns/V

#### **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T <sub>A</sub> = 25°C		
Symbol	Characteristic	Тур	Max	Unit
VOLP	Quiet Output Maximum Dynamic VOL	0.3	0.8	V
VOLV	Quiet Output Minimum Dynamic V <sub>OL</sub>	- 0.3	- 0.8	V
VIHD	Minimum High Level Dynamic Input Voltage		3.5	V
V <sub>ILD</sub>	Maximum Low Level Dynamic Input Voltage		1.5	V

Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

#### DC ELECTRICAL CHARACTERISTICS

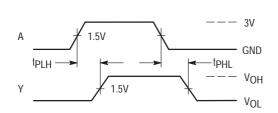
			VCC	Т	A = 25°	C	T <sub>A</sub> ≤	85°C	T <sub>A</sub> ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
VIH	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
V <sub>IL</sub>	Maximum Low–Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
VOH	Minimum High–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50\mu\text{A}$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	VIN = VIH or VIL	V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OH</sub> = -4mA I <sub>OH</sub> = -8mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
VOL	Maximum Low–Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu A$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or $V_{IL}$	VIN = VIH or VIL IOL = 4mA IOL = 8mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5V or GND	0 to 5.5			±0.1	-	±1.0		±1.0	μА
ICC	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5	.0	76.	2.0	17	20		40	μΑ
ICCT	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4V	5.5	36	OV	1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5V	0.0	,0		0.5		5.0		10	μА

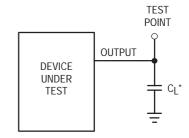
#### AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0$ ns)

					T <sub>A</sub> = 25°C		$T_A = -40$	) to 85°C	
Symbol	Parameter	Test Condit	tions	Min	Тур	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A or B to Y	$V_{CC} = 3.3 \pm 0.3 V$	$C_L = 15pF$ $C_L = 50pF$		5.5 8.0	7.9 11.4	1.0 1.0	9.5 13.0	ns
		$V_{CC} = 5.0 \pm 0.5 V$	$C_L = 15pF$ $C_L = 50pF$		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5	
C <sub>in</sub>	Maximum Input Capacitance				4	10		10	рF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
C <sub>PD</sub>	Power Dissipation Capacitance (Note 1.)	22	pF

<sup>1.</sup> CpD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: ICC(OPR) = CpD • VcC • f<sub>in</sub> + I<sub>CC</sub>/4 (per gate). CpD is used to determine the no–load dynamic power consumption; PD = CpD • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.





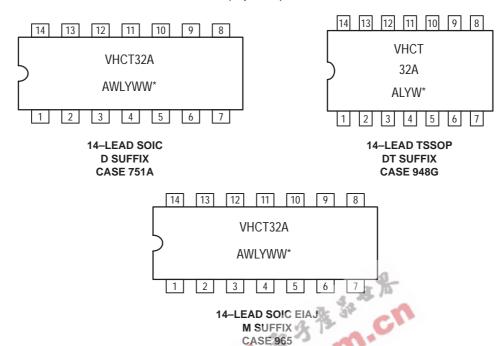
\*Includes all probe and jig capacitance

Figure 1. Switching Waveforms

Figure 2. Test Circuit

#### **MARKING DIAGRAMS**

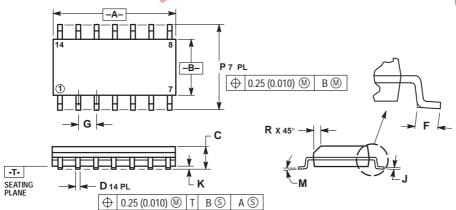
(Top View)



\*See Applications Note #AND8004/D for date code and traceability information.

#### **PACKAGE DIMENSIONS**

#### **D SUFFIX** PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.

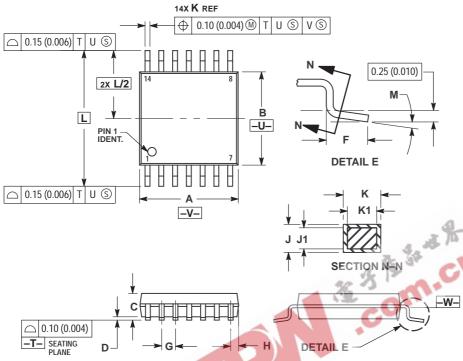
- DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- PER SIDE.
  DIMENSION D DOES NOT INCLUDE DAMBAR

PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIM	MILLIMETERS I			
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

#### **PACKAGE DIMENSIONS**

#### **DT SUFFIX** PLASTIC TSSOP PACKAGE CASE 948G-01 **ISSUE O**



- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION, ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM

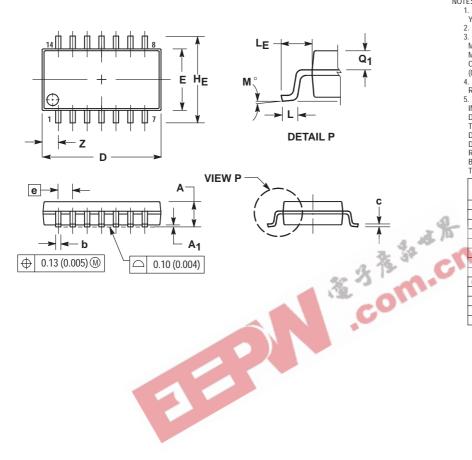
  - EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
    TERMINAL NUMBERS ARE SHOWN FOR
- REFERENCE ONLY.
  DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
Н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252 BSC		
М	0°	8°	0°	8°	

#### PACKAGE DIMENSIONS

#### **M SUFFIX**

PLASTIC SOIC EIAJ PACKAGE CASE 965-01 **ISSUE O** 



#### NOTES:

- 11ES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDL.
  4. TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	METERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
LΕ	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	) BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LF	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10 °
Q <sub>1</sub>	0.70	0.90	0.028	0.035
7		1.42		0.054

## **Notes**





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